



6N90Z

Preliminary

Power MOSFET

**6.2A, 900V N-CHANNEL
POWER MOSFET**

■ DESCRIPTION

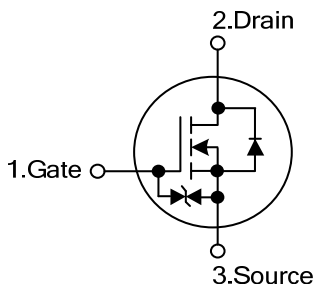
The UTC **6N90Z** is an N-channel enhancement mode power MOSFET using UTC's advanced technology to provide costumers with planar stripe and DMOS technology. This technology allows a minimum on-state resistance and superior switching performance. It also can withstand high energy pulse in the avalanche and commutation mode.

The UTC **6N90Z** is generally applied in high efficiency switch mode power supplies.

■ FEATURES

- * $R_{DS(ON)} < 2.3\Omega @ V_{GS} = 10V$
- * Fast switching
- * 100% avalanche tested
- * Improved dv/dt capability

■ SYMBOL



■ ORDERING INFORMATION

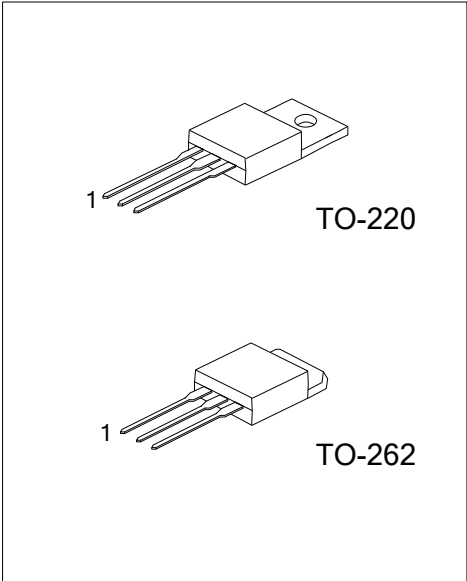
Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
6N90ZL-TA3-T	6N90ZG-TA3-T	TO-220	G	D	S	Tube
6N90ZL-TQ2-T	6N90ZG-TQ2-T	TO-262	G	D	S	Tube

Note: Pin Assignment: G: Gate D: Drain S: Source

<p>6N90ZL-TA3-T</p> <p>(1)Packing Type</p> <p>(2)Package Type</p> <p>(3)Lead Free</p>	<p>(1) T: Tube</p> <p>(2) TA3: TO-220, TQ2: TO-262</p> <p>(3) L: Lead Free, G: Halogen Free</p>
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■ MARKING INFORMATION

PACKAGE	MARKING
TO-220 TO-262	<p>UTC 6N90Z</p> <p>Lot Code ← [] [] [] [] [] → Data Code</p> <p>L: Lead Free G: Halogen Free</p> <p>1</p>



■ ABSOLUTE MAXIMUM RATINGS ($T_C=25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	RATINGS	UNIT
Drain-Source Voltage	V_{DSS}	900	V
Gate-Source Voltage	V_{GSS}	± 20	V
Drain Current	Continuous ($T_C=25^\circ\text{C}$)	I_D	6.2
	Pulsed (Note 2)	I_{DM}	24
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	300
	Repetitive (Note 2)	E_{AR}	16.7
Peak Diode Recovery dv/dt (Note 4)	dv/dt	4.5	V/ns
Power Dissipation	P_D	125	W
Junction Temperature	T_J	+150	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55~+150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature

3. $L = 16.6\text{mH}$, $I_{AS} = 6\text{A}$, $V_{DD} = 50\text{V}$, $R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$

4. $I_{SD} \leq 6\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$

■ THERMAL CHARACTERISTICS

PARAMETER	SYMBOL	RATINGS	UNIT
Junction to Ambient	θ_{JA}	62.5	$^\circ\text{C}/\text{W}$
Junction to Case	θ_{JC}	1	$^\circ\text{C}/\text{W}$

■ ELECTRICAL CHARACTERISTICS ($T_C=25^\circ\text{C}$, unless otherwise specified)

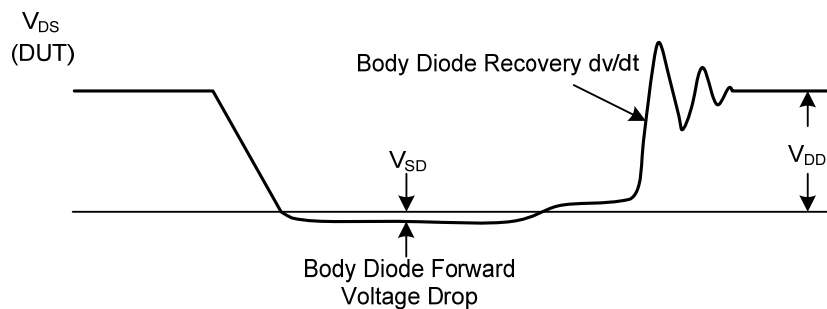
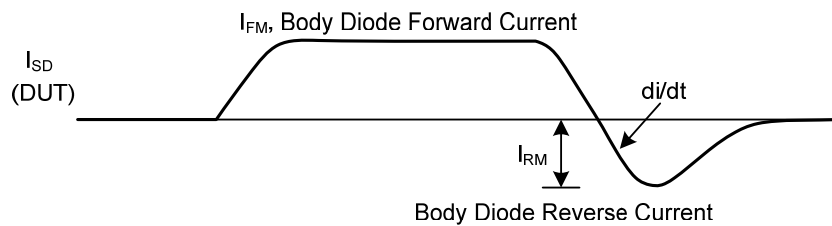
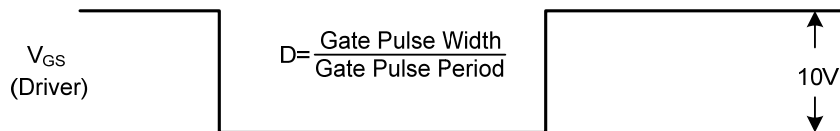
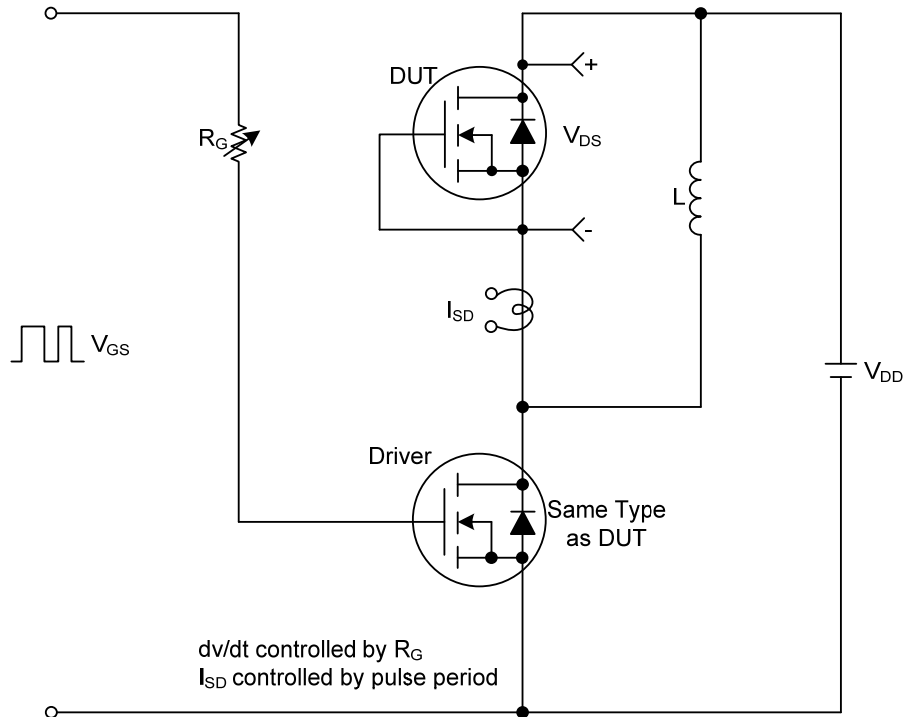
PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV_{DSS}	$I_D=250\mu\text{A}$, $V_{GS}=0\text{V}$	900			V
Breakdown Voltage Temperature Coefficient	$\Delta BV_{DSS}/\Delta T_J$	Reference to 25°C , $I_D=250\mu\text{A}$		1.07		$\text{V}/^\circ\text{C}$
Drain-Source Leakage Current	I_{DSS}	$V_{DS}=900\text{V}$, $V_{GS}=0\text{V}$			10	μA
Gate- Source Leakage Current	Forward	I_{GSS}			+5	μA
	Reverse				-5	μA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{DS}=V_{GS}$, $I_D=250\mu\text{A}$	3.0		5.0	V
Static Drain-Source On-State Resistance	$R_{DS(ON)}$	$V_{GS}=10\text{V}$, $I_D=3.1\text{A}$		1.72	2.3	Ω
DYNAMIC PARAMETERS						
Input Capacitance	C_{ISS}	$V_{GS}=0\text{V}$, $V_{DS}=25\text{V}$, $f=1.0\text{MHz}$		1270	1770	pF
Output Capacitance	C_{OSS}			110	145	pF
Reverse Transfer Capacitance	C_{RSS}			15	25	pF
SWITCHING PARAMETERS						
Total Gate Charge	Q_G	$V_{GS}=10\text{V}$, $V_{DS}=50\text{V}$, $I_D=1.3\text{A}$ (Note 1, 2)		45	55	nC
Gate to Source Charge	Q_{GS}			5		nC
Gate to Drain Charge	Q_{GD}			13		nC
Turn-ON Delay Time	$t_{D(ON)}$	$V_{DD}=30\text{V}$, $I_D=1\text{A}$, $R_G=25\Omega$ (Note 1, 2)		80	110	ns
Rise Time	t_R			100	150	ns
Turn-OFF Delay Time	$t_{D(OFF)}$			210	250	ns
Fall-Time	t_F			125	145	ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Body-Diode Continuous Current	I_S				6.2	A
Maximum Body-Diode Pulsed Current	I_{SM}				24.8	A
Drain-Source Diode Forward Voltage	V_{SD}	$I_S=6.2\text{A}$, $V_{GS}=0\text{V}$			1.4	V
Body Diode Reverse Recovery Time	t_{RR}	$I_S=6.2\text{A}$, $V_{GS}=0\text{V}$, $dI_F/dt=100\text{A}/\mu\text{s}$		630		ns
Body Diode Reverse Recovery Charge	Q_{RR}	(Note 1)		6.9		μC

Notes: 1. Pulse Test: Pulse width $\leq 300\mu\text{s}$, Duty cycle $\leq 2\%$

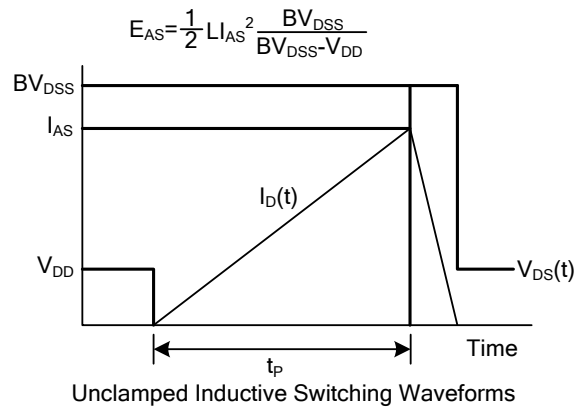
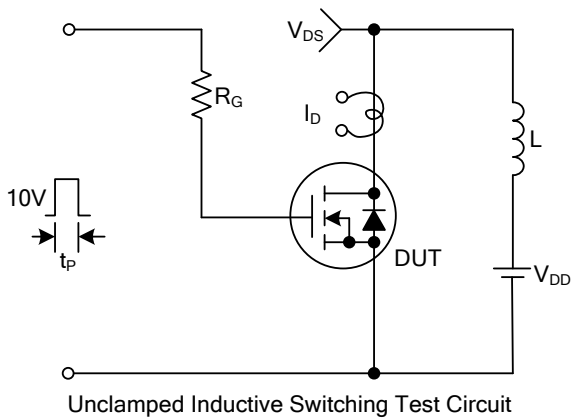
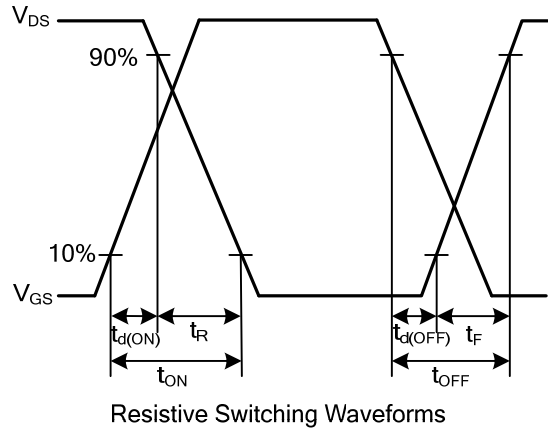
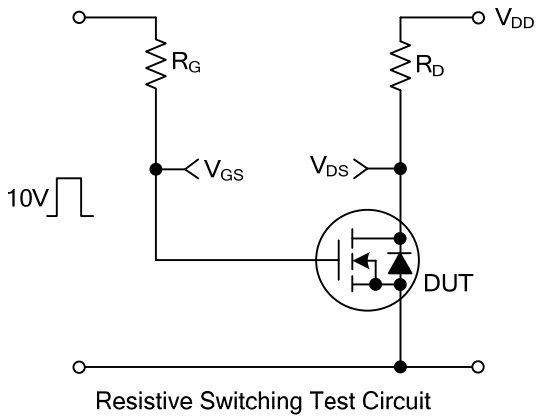
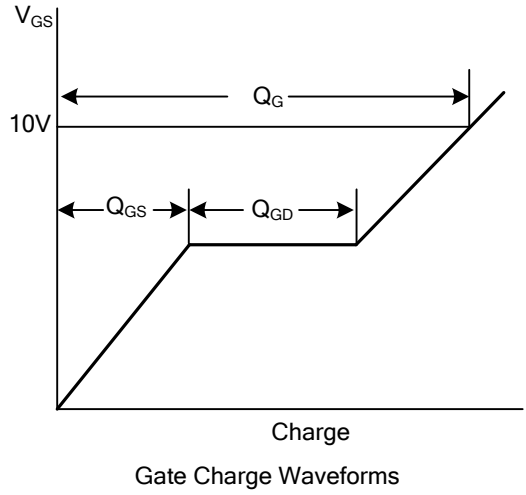
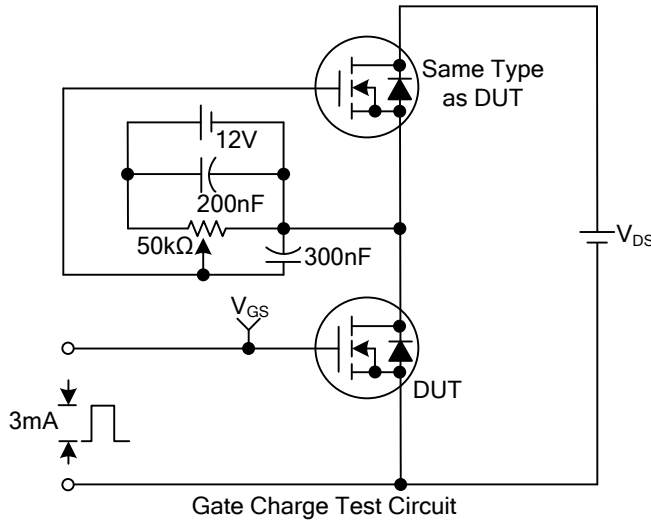
2. Essentially independent of operating temperature

■ TEST CIRCUITS AND WAVEFORMS

Peak Diode Recovery dv/dt Test Circuit & Waveforms



■ TEST CIRCUITS AND WAVEFORMS(Cont.)



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